

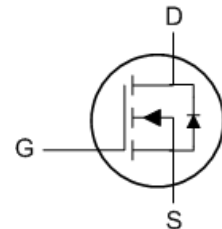
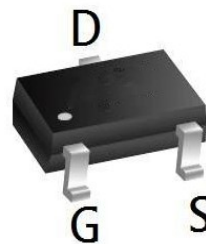
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology


Product Summary

BVDSS	R _{DS(on)}	I _D
30V	12mΩ	7.0A

Description

The AO3410L is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(on)} and efficiency for most of the small power switching and load switch applications. The AO3410L meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	7.0	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	5.5	A
I _{DM}	Pulsed Drain Current ²	29.4	A
P _D @T _A =25°C	Total Power Dissipation ³	2.0	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	---	°C/W

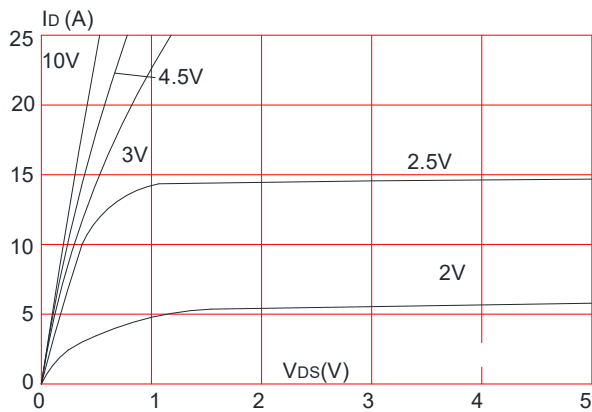
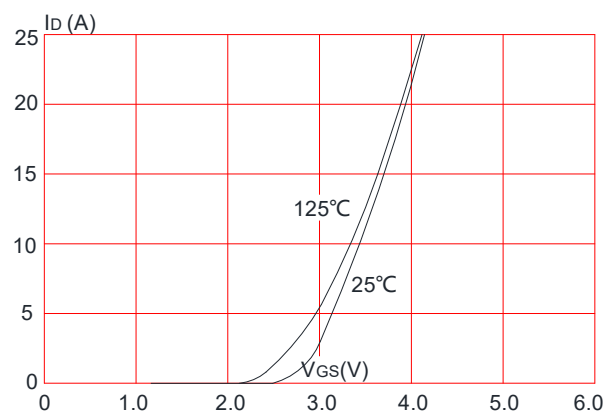
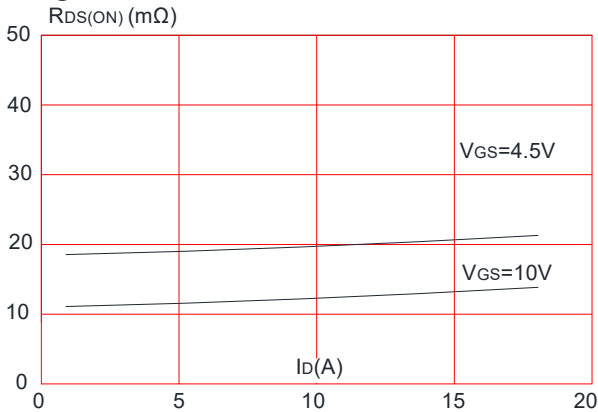
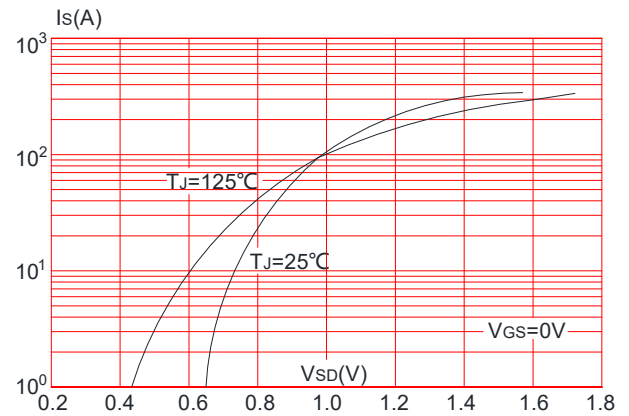
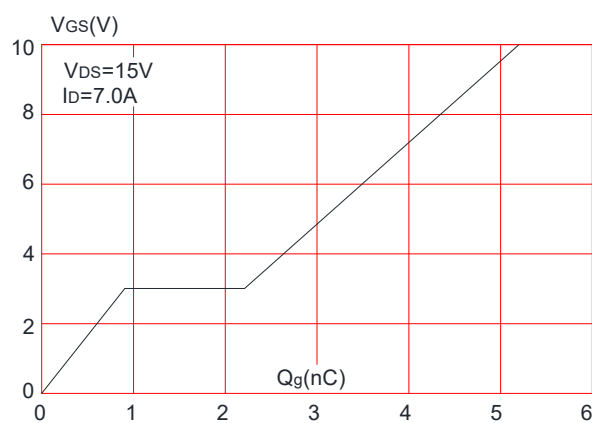
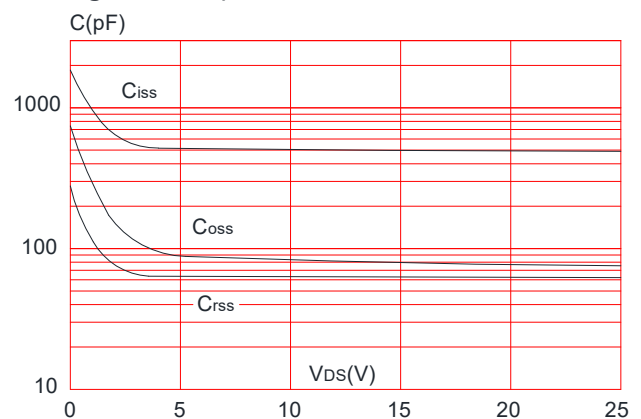
Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

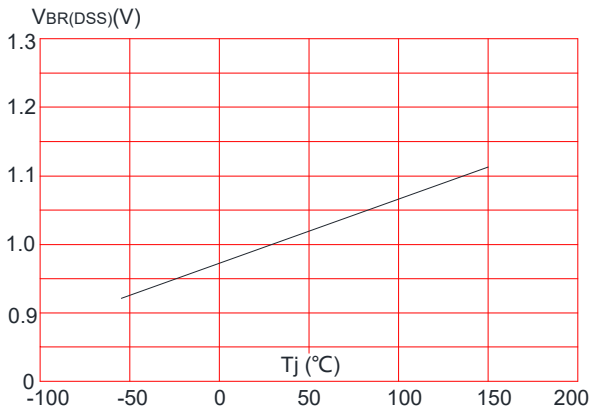
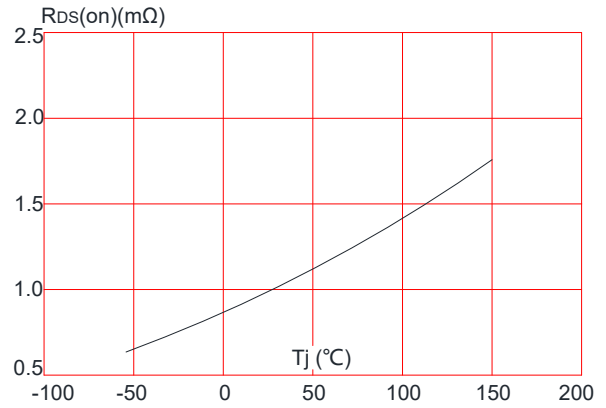
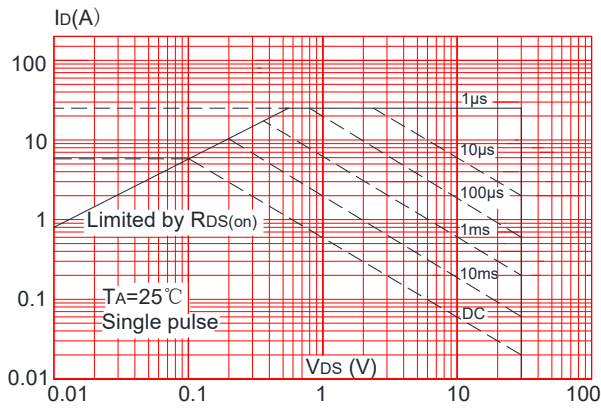
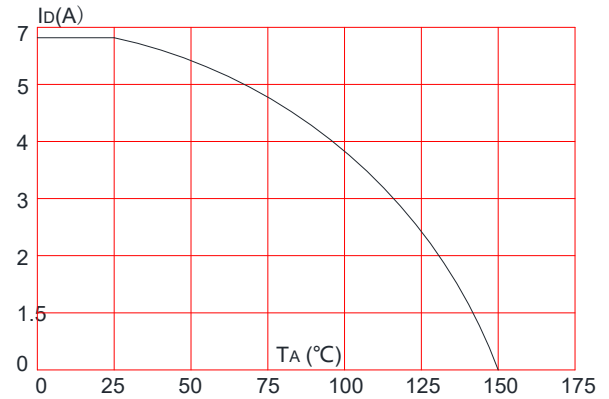
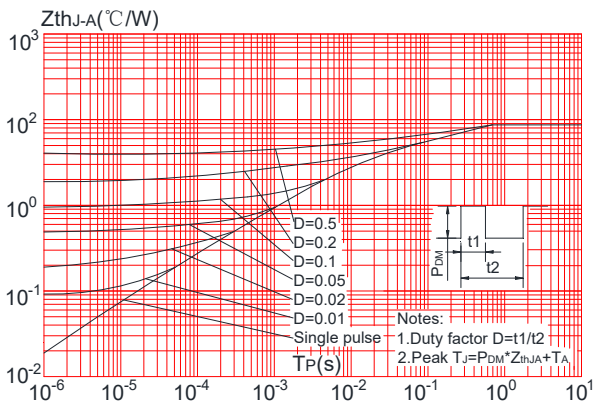
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=10A$	-	12	17	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	17	25	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	614	-	pF
C_{oss}	Output Capacitance		-	118	-	pF
C_{rss}	Reverse Transfer Capacitance		-	98	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=11A,$ $V_{GS}=10V$	-	16	-	nC
Q_{gs}	Gate-Source Charge		-	2.7	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	4.5	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V, R_L=1.35\Omega,$ $R_{GEN}=3\Omega, V_{GS}=10V$	-	6	-	ns
t_r	Turn-on Rise Time		-	10	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	30	-	ns
t_f	Turn-off Fall Time		-	6.5	-	ns
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=15A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=11A, di/dt=500A/\mu s$	-	7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		$T_J=25^\circ C$	-	10	-

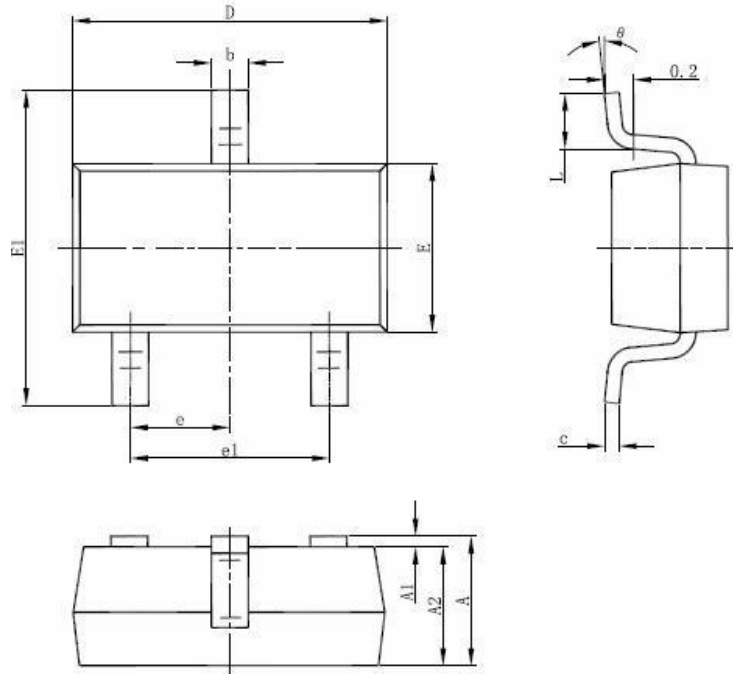
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	7	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=8A, di/dt=100A/\mu s,$ $T_J=25^\circ C$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.9	---	nC

Note :

N-Ch 30V Fast Switching MOSFETs
Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


N-Ch 30V Fast Switching MOSFETs
Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


SOT-23-3L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°